

ABSTRACT OF THE DISCLOSURE

In a thin-film insulated gate type field effect transistor having a metal gate in which the surface of the gate electrode is subjected to anodic oxidation, a silicon nitride film is provided so as to be interposed between the gate electrode and the gate insulating film to prevent invasion of movable ions into a channel, and also to prevent the breakdown of the gate insulating film due to a potential difference between the gate electrode and the channel region. By coating a specific portion of the gate electrode with metal material such as chrome or the like for the anodic oxidation, and then removing only the metal material such as chrome or the like together with the anodic oxide of the metal material such as chrome or the like, an exposed portion of metal gate (e.g. aluminum) is formed, and an upper wiring is connected to the exposed portion. Further, an aluminum oxide or silicon nitride is formed as an etching stopper between the gate electrode and the gate insulating film or between the substrate and the layer on the substrate, so that the over-etching can be prevented and the flatness of the element can be improved. In addition, a contact is formed in no consideration of the concept "contact hole".

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